### SONY

# ICX408ALB

### Diagonal 6mm (Type 1/3) CCD Image Sensor for EIA B/W Video Cameras

### Description

The ICX408ALB is an interline CCD solid-state image sensor suitable for EIA B/W video cameras with a diagonal 6mm (Type 1/3) system. Compared with the current product ICX058ALB, basic characteristics such as sensitivity, smear, dynamic range and S/N are improved drastically.

This chip features a field period readout system and an electronic shutter with variable charge-storage time. Also, this outline is miniaturized by using original package.

This chip is suitable for applications such as surveillance cameras, automative cameras, etc.

### **Features**

- High sensitivity (+5dB compared with the ICX058ALB)
- Low smear (-15dB compared with the ICX058ALB)
- High D range (+4dB compared with the ICX058ALB)
- High S/N
- High resolution and low dark current
- Excellent antiblooming characteristics
- Continuous variable-speed shutter
- · No voltage adjustment

(Reset gate and substrate bias are not adjusted.)

Horizontal register: 5V drive Reset gate pulse: 5V drive

### **Device Structure**

• Interline CCD image sensor

• Optical size: Diagonal 6mm (Type 1/3)

• Number of effective pixels: 768 (H)  $\times$  494 (V) approx. 380K pixels • Total number of pixels: 811 (H)  $\times$  508 (V) approx. 410K pixels

 $\bullet \mbox{ Chip size:} \qquad \qquad 5.59 \mbox{mm (H)} \times 4.68 \mbox{mm (V)} \\ \bullet \mbox{ Unit cell size:} \qquad \qquad 6.35 \mbox{\mum (H)} \times 7.40 \mbox{\mum (V)}$ 

Optical black: Horizontal (H) direction: Front 3 pixels, rear 40 pixels

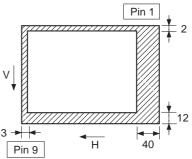
Vertical (V) direction: Front 12 pixels, rear 2 pixels

Number of dummy bits: Horizontal 22

Vertical 1 (even fields only)

• Substrate material: Silicon

# 14 pin DIP (Ceramic)



Optical black position (Top View)

## Super HAD CCD TM

\* Super HAD CCD is a trademark of Sony Corporation. The Super HAD CCD is a version of Sony's high performance CCD HAD (Hole-Accumulation Diode) sensor with sharply improved sensitivity by the incorporation of a new semiconductor technology developed by Sony Corporation.

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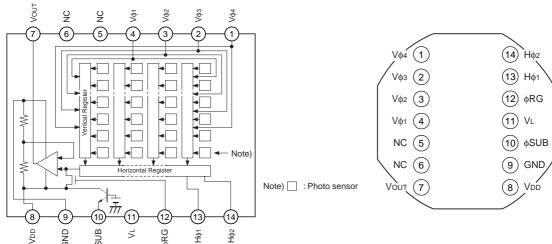
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### **Block Diagram and Pin Configuration**

(Top View)



### **Pin Description**

Pin No.	Symbol	Description	Pin No.	Symbol	Description
1	Vф4	Vertical register transfer clock	8	VDD	Supply voltage
2	Vф3	Vertical register transfer clock	9	GND	GND
3	Vф2	Vertical register transfer clock	10	φSUB	Substrate clock
4	Vф1	Vertical register transfer clock	11	VL	Protective transistor bias
5	NC		12	φRG	Reset gate clock
6	NC		13	Нф1	Horizontal register transfer clock
7	Vout	Signal output	14	Нф2	Horizontal register transfer clock

### **Absolute Maximum Ratings**

	Item	Ratings	Unit	Remarks
	Vdd, Vout, RG – фSUB	-40 to +8	V	
Against &CLIP	Vφ1, Vφ3 – φSUB	-50 to +15	V	
Against	$V\phi_2$ , $V\phi_4$ , $V_L - \phi SUB$	-50 to +0.3	V	
	Hφ1, Hφ2, GNG – φSUB	-40 to +8 V  -50 to +15 V  -50 to +0.3 V  -40 to +0.3 V  -40 to +0.3 V  -0.3 to +20 V  -10 to +18 V  -10 to +6 V  -0.3 to +28 V  -0.3 to +15 V	V	
	Vdd, Vout, RG – GND	-0.3 to +20	V	
Against GND	Vφ1, Vφ2, Vφ3, Vφ4 – GND	-10 to +18	V	
	Hφ1, Hφ2 – GND	-10 to +6	V	
Against \/	Vφ1, Vφ3 – VL	-0.3 to +28	V	
Against V∟	Vφ2, Vφ4, Hφ1, Hφ2, GND – VL	-0.3 to +15	V	
Detuces insut alcale	Voltage difference between horizontal clock input pins	to +15	V	*1
Between input clock pins	Hφ1 – Hφ2	-6 to +6	V	
,	Hφ1, Hφ2 – Vφ4	-14 to +14	V	
Storage temperature		-30 to +80	°C	
Operating temperatu	ıre	-10 to +60	°C	

 $<sup>^{*1}</sup>$  +24V (Max.) when clock width < 10 $\mu$ s, clock duty factor < 0.1%.

### **Bias Conditions**

Item	Symbol	Min.	Тур.	Max.	Unit	Remarks
Supply voltage	VDD	14.55	15.0	15.45	V	
Protective transistor bias	VL		*1			
Substrate clock	φSUB		*2			

<sup>\*1</sup> VL setting is the VvL voltage of the vertical transfer clock waveform, or the same supply voltage as the VL power supply for the V driver should be used.

### **DC Characteristics**

Item	Symbol	Min.	Тур.	Max.	Unit	Remarks
Supply current	IDD		4	6	mA	

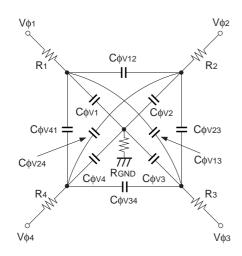
### **Clock Voltage Conditions**

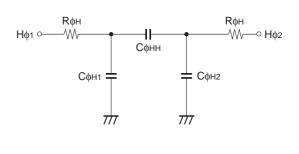
Item	Symbol	Min.	Тур.	Max.	Unit	Waveform diagram	Remarks
Readout clock voltage	Vvт	14.55	15.0	15.45	V	1	
	VvH1, VvH2	-0.05	0	0.05	V	2	$V_{VH} = (V_{VH1} + V_{VH2})/2$
	VvH3, VvH4	-0.2	0	0.05	V	2	
	VVL1, VVL2, VVL3, VVL4	-8.0	-7.0	-6.5	V	2	Vvl = (Vvl3 + Vvl4)/2
	Vφv	6.3	7.0	8.05	V	2	$V\phi V = VVHN - VVLN (n = 1 to 4)$
Vertical transfer clock	Vvнз — Vvн	-0.25		0.1	V	2	
voltage	Vvh4 – Vvh	-0.25		0.1	V	2	
	Vvнн			0.3	V	2	High-level coupling
	Vvhl			0.3	V	2	High-level coupling
	VVLH			0.3	V	2	Low-level coupling
	Vvll			0.3	V	2	Low-level coupling
Horizontal transfer	Vфн	4.75	5.0	5.25	V	3	
clock voltage	VHL	-0.05	0	0.05	V	3	
	Vørg	4.5	5.0	5.5	٧	4	Input through 0.1µF capacitance
Reset gate clock	Vrglh – Vrgll			0.4	V	4	Low-level coupling
voltage	VRGL - VRGLm		5.0	0.5	V	4	Low-level coupling
	Vrgh	V <sub>DD</sub> +0.3	V <sub>DD</sub> +0.6	V <sub>DD</sub> +0.9	V	4	
Substrate clock voltage	Vфѕив	21.0	22.0	23.5	V	5	

<sup>\*2</sup> Do not apply a DC bias to the substrate clock pin, because a DC bias is generated within the CCD.

### **Clock Equivalent Circuit Constant**

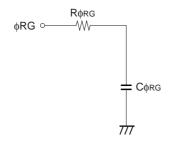
Item	Symbol	Min.	Тур.	Max.	Unit	Remarks
Capacitance between vertical transfer clock	Сф∨1, Сф∨3		1500		pF	
and GND	Сф∨2, Сф∨4		1000		pF	
	СфV12, СфV34		820		pF	
Canacitanes between vertical transfer clocks	Сф∨23, Сф∨41		330		pF	
Capacitance between vertical transfer clocks	Сф513		120		pF	
	<b>C</b> φς24		100		pF	
Capacitance between horizontal transfer clock and GND	Сфн1, Сфн2		75		pF	
Capacitance between horizontal transfer clocks	Сфнн		22		pF	
Capacitance between reset gate clock and GND	СфRG		5		pF	
Capacitance between substrate clock and GND	Сфѕив		270		pF	
Ventical transfer also les conics assistant	R1, R3		100		Ω	
Vertical transfer clock series resistor	R2, R4		150		Ω	
Vertical transfer clock ground resistor	RGND		68		Ω	
Horizontal transfer clock series resistor	Rфн		15		Ω	
Reset gate clock series resistor	Rørg		50		Ω	





Vertical transfer clock equivalent circuit

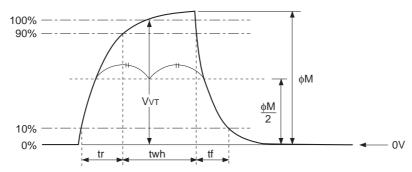
Horizontal transfer clock equivalent circuit



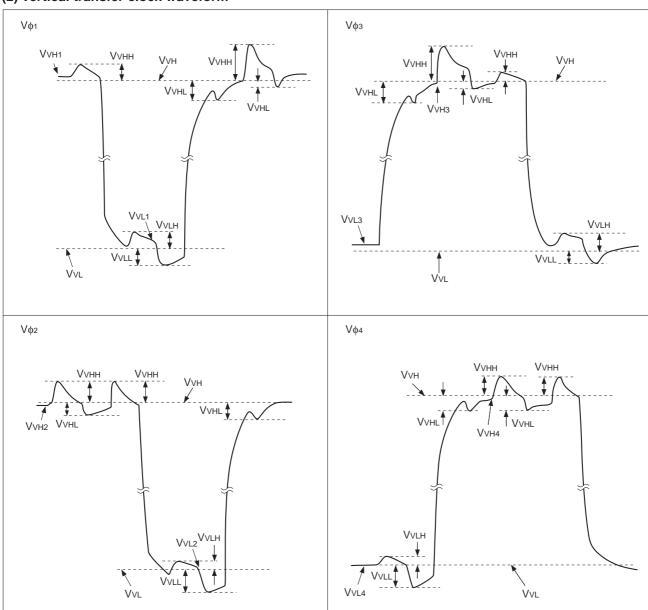
Reset gate clock equivalent circuit

### **Drive Clock Waveform Conditions**

### (1) Readout clock waveform



### (2) Vertical transfer clock waveform

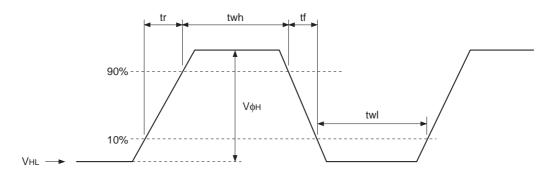


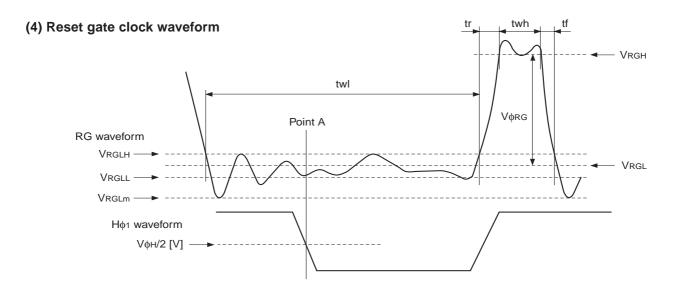
VvH = (VvH1 + VvH2)/2

 $V_{VL} = (V_{VL3} + V_{VL4})/2$ 

 $V\phi V = VVHN - VVLN (n = 1 to 4)$ 

### (3) Horizontal transfer clock waveform





VRGLH is the maximum value and VRGLL is the minimum value of the coupling waveform during the period from Point A in the above diagram until the rising edge of RG. In addition, VRGL is the average value of VRGLH and VRGLL.

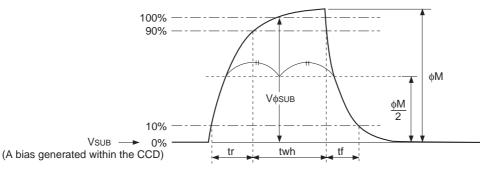
$$V_{RGL} = (V_{RGLH} + V_{RGLL})/2$$

Assuming VRGH is the minimum value during the period twh, then:

$$V\phi RG = VRGH - VRGL$$

Negative overshoot level during the falling edge of RG is VRGLm.

### (5) Substrate clock waveform



### **Clock Switching Characteristics**

	ltom	Symbol		twh			twl			tr			tf		Unit	Domorko	
	Item	Symbol	Min.	Тур.	Мах.	Unit	Remarks										
Rea	adout clock	VT	2.3	2.5						0.5			0.5		μs	During readout	
Ver	tical transfer ck	Vφ1, Vφ2, Vφ3, Vφ4										15		250	ns	*1	
~	During	Нф1	26	28.5		26	28.5			6.5	9.5		6.5	9.5	ns	*2	
cloc	imaging	Нф2	26	28.5		26	28.5			6.5	9.5		6.5	9.5	110		
Horizontal transfer clock	During	Нф1		5.38						0.01			0.01		μs		
Hz tra	parallel-serial conversion	Нф2					5.38			0.01			0.01				
Res	set gate clock	φRG	11	13			51			3			3		ns		
Sub	strate clock	φSUB	1.5	1.8							0.5			0.5	μs	When draining charge	

<sup>\*1</sup> When vertical transfer clock driver CXD1267AN is used.

<sup>\*2</sup> tf  $\geq$  tr - 2ns, and the cross-point voltage (VCR) for the H $\phi$ 1 rising side of the H $\phi$ 1 and H $\phi$ 2 waveforms must be at least V $\phi$ H/2 [V].

Itom	Symbol		two		Lloit	Domorko	
Item	Symbol	Min.	Тур.	Max.	Uniii	Remarks	
Horizontal transfer clock	Нф1, Нф2	22	26		ns	*3	

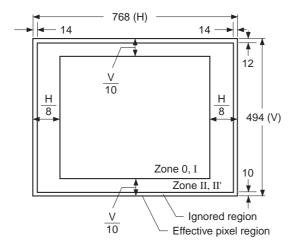
<sup>\*3</sup> The overlap period for twh and twl of horizontal transfer clocks  $H\phi_1$  and  $H\phi_2$  is two.

### **Image Sensor Characteristics**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Min.	Тур.	Max.	Unit	Measurement method	Remarks
Sensitivity	S	680	850		mV	1	Ta = 60°C
Saturation signal	Vsat	1000			mV	2	
Smear	Sm		-110	-93	dB	3	
Att day a language of the all and	SH			20	%	4	Zone 0 and I
Video signal shading	эп			25	%	4	Zone 0 to II'
Dark signal	Vdt			2	mV	5	Ta = 60°C
Dark signal shading	ΔVdt			1	mV	6	Ta = 60°C
Flicker	F			2	%	7	
Lag	Lag			0.5	%	8	

### **Zone Definition of Video Signal Shading**



### **Image Sensor Characteristics Measurement Method**

### Measurement conditions

 In the following measurements, the device drive conditions are at the typical values of the bias and clock voltage conditions.

2) In the following measurements, spot blemishes are excluded and, unless otherwise specified, the optical black (OB) level is used as the reference for the signal output, and the value measured at the point [\*A] in the Drive Circuit is used.

### Definition of standard imaging conditions

### 1) Standard imaging condition I:

Use a pattern box (luminance  $706cd/m^2$ , color temperature of 3200K halogen source) as a subject. (Pattern for evaluation is not applicable.) Use a testing standard lens with CM500S (t = 1.0mm) as an IR cut filter and image at F8. The luminous intensity to the sensor receiving surface at this point is defined as the standard sensitivity testing luminous intensity.

### 2) Standard imaging condition II:

Image a light source (color temperature of 3200K) with a uniformity of brightness within 2% at all angles. Use a testing standard lens with CM500S (t = 1.0mm) as an IR cut filter. The luminous intensity is adjusted to the value indicated in each testing item by the lens diaphragm.

### 1. Sensitivity

Set to standard imaging condition I. After selecting the electronic shutter mode with a shutter speed of 1/250s, measure the signal output (Vs) at the center of the screen and substitute the value into the following formula.

$$S = Vs \times \frac{250}{60} [mV]$$

### 2. Saturation signal

Set to standard imaging condition II. After adjusting the luminous intensity to 10 times the intensity with average value of the signal output, 200mV, measure the minimum value of the signal output.

### 3. Smear

Set to standard imaging condition II. With the lens diaphragm at F5.6 to F8, adjust the luminous intensity to 500 times the intensity with average value of the signal output, 200mV. When the readout clock is stopped and the charge drain is executed by the electronic shutter at the respective H blankings, measure the maximum value (VSm [mV]) of the signal output and substitute the value into the following formula.

$$Sm = 20 \times log \left( \frac{VSm}{200} \times \frac{1}{500} \times \frac{1}{10} \right) \text{ [dB]} \quad (1/10V \text{ method conversion value)}$$

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### 4. Video signal shading

Set to standard imaging condition II. With the lens diaphragm at F5.6 to F8, adjust the luminous intensity so that the average value of the signal output is 200mV. Then measure the maximum (Vmax [mV]) and minimum (Vmin [mV]) values of the signal output and substitute the values into the following formula.

$$SH = (Vmax - Vmin)/200 \times 100 [\%]$$

### 5. Dark signal

Measure the average value of the signal output (Vdt [mV]) with the device ambient temperature 60°C and the device in the light-obstructed state, using the horizontal idle transfer level as a reference.

### 6. Dark signal shading

After measuring 5, measure the maximum (Vdmax [mV]) and minimum (Vdmin [mV]) values of the dark signal output and substitute the values into the following formula.

$$\Delta Vdt = Vdmax - Vdmin [mV]$$

### 7. Flicker

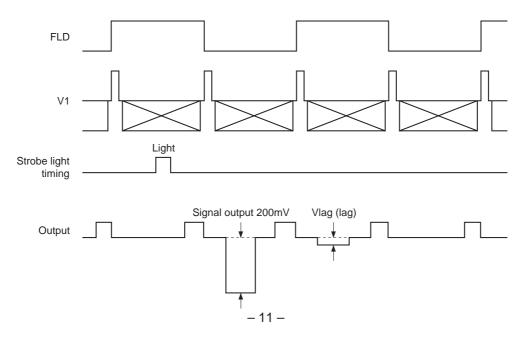
Set to standard imaging condition II. Adjust the luminous intensity so that the average value of the signal output is 200mV, and then measure the difference in the signal level between fields ( $\Delta$ Vf [mV]). Then substitute the value into the following formula.

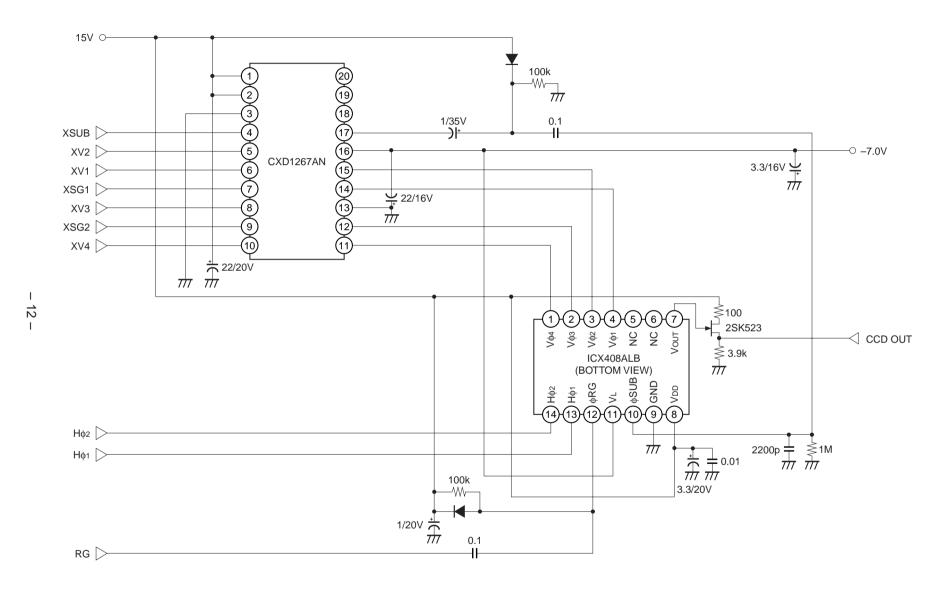
$$F = (\Delta Vf/200) \times 100 [\%]$$

### 8. Lag

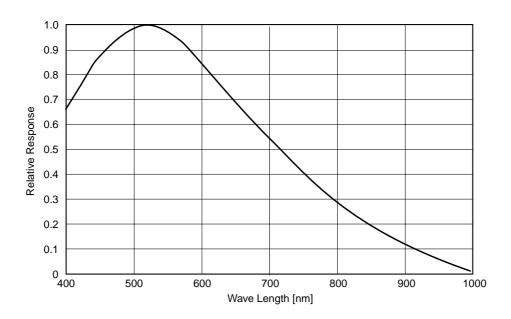
Adjust the signal output value generated by strobe light to 200mV. After setting the strobe light so that it strobes with the following timing, measure the residual signal (Vlag). Substitute the value into the following formula.

$$Lag = (Vlag/200) \times 100 [\%]$$

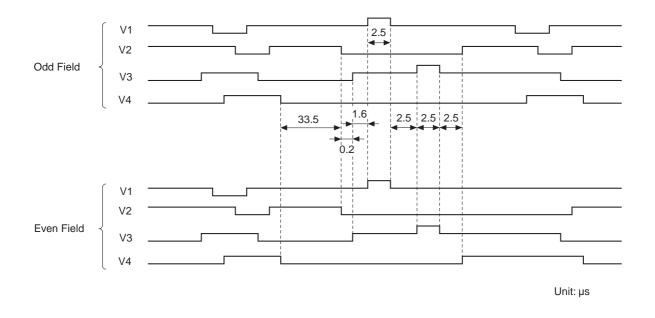


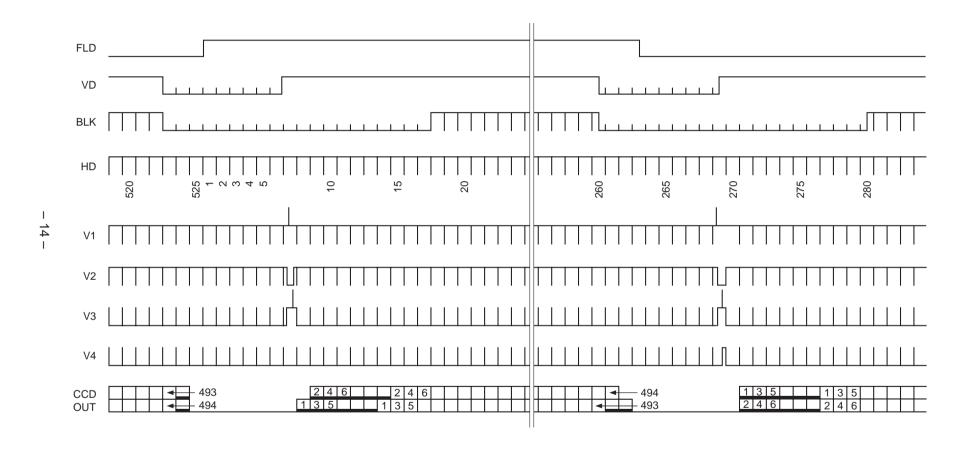


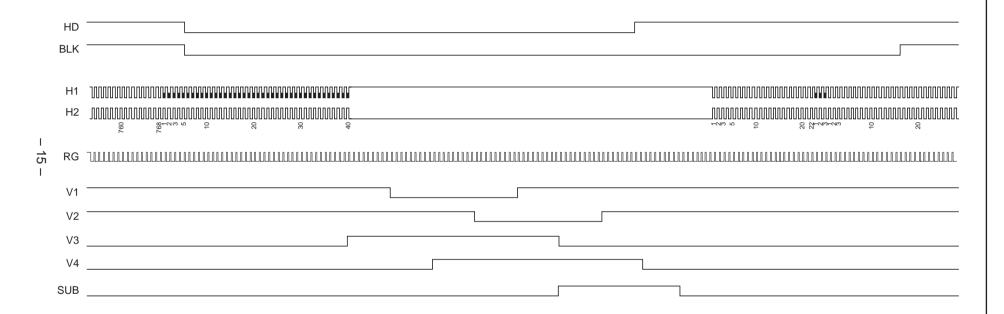
Spectral Sensitivity Characteristics (Excludes lens characteristics and light source characteristics)



### **Sensor Readout Clock Timing Chart**







### **Notes on Handling**

### 1) Static charge prevention

CCD image sensors are easily damaged by static discharge. Before handling be sure to take the following protective measures.

- a) Either handle bare handed or use non-chargeable gloves, clothes or material.
   Also use conductive shoes.
- b) When handling directly use an earth band.
- c) Install a conductive mat on the floor or working table to prevent the generation of static electricity.
- d) Ionized air is recommended for discharge when handling CCD image sensor.
- e) For the shipment of mounted substrates, use boxes treated for the prevention of static charges.

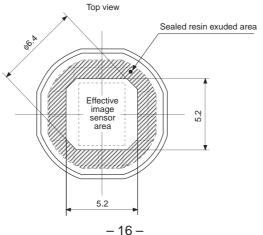
### 2) Soldering

- a) Make sure the package temperature does not exceed 80°C.
- b) Solder dipping in a mounting furnace causes damage to the glass and other defects. Use a 30W soldering iron with a ground wire and solder each pin in less than 2 seconds. For repairs and remount, cool sufficiently.
- c) To dismount an image sensor, do not use a solder suction equipment. When using an electric desoldering tool, use a thermal controller of the zero cross On/Off type and connect it to ground.

### 3) Dust and dirt protection

Image sensors are packed and delivered by taking care of protecting its glass plates from harmful dust and dirt. Clean glass plates with the following operation as required, and use them.

- a) Operate in clean environments (aronud class 1000 is appropriate).
- b) Do not either touch glass plates by hand or have any object come in contact with glass surfaces. Should dirt stick to a glass surface, blow it off with an air blower. (For dirt stuck through static electricity ionized air is recommended.)
- c) Clean with a cotton bud and ethyl alcohol if the grease stained. Be careful not to scratch the glass.
- d) Keep in a case to protect from dust and dirt. To prevent dew condensation, preheat or precool when moving to a room with great temperature differences.
- e) When a protective tape is applied before shipping, just before use remove the tape applied for electrostatic protection. Do not reuse the tape.
- 4) Do not expose to strong light (sun rays) for long periods. For continuous using under cruel condition exceeding the normal using condition, consult our company.
- 5) Exposure to high temperature or humidity will affect the characteristics. Accordingly avoid storage or usage in such conditions.
- 6) CCD image sensors are precise optical equipment that should not be subject to too much mechanical shocka.
- 7) Eclipse (to get dark around the four corners of the picture) may occur when some object lenses are in the open iris state.

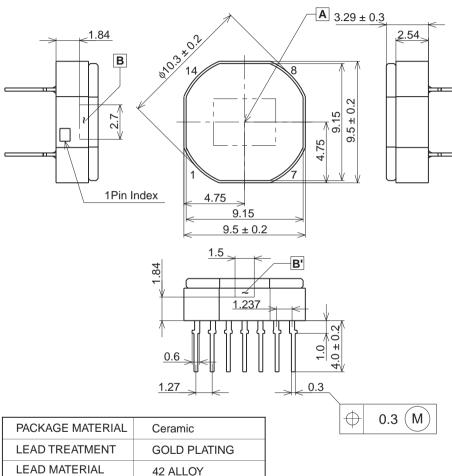


PACKAGE MASS

DRAWING NUMBER

0.60g

AS-C3-02(E)



5.08	~	3.5
	7	V

C

0.25

- 1. "A" is the center of the effective image area.
- 2. The point "B" of the package is the horizontal reference. The point "B" of the package is the vertical reference.
- 3. The bottom "C" of the package is the height reference.
- 4. The center of the effective image area relative to the center of the package (\*) is  $(H, V) = (0.0) \pm 0.15$ mm.
- 5. The rotation angle of the effective image area relative to H and V is  $\pm 1^{\circ}$ .
- 6. The height from the bottom "C" to the effective image area is  $1.41 \pm 0.15$ mm.
- 7. The tilt of the effective image area relative to the bottom "C" is less than 60µm.
- 8. The thickness of the cover glass is 0.75mm, and the refractive index is 1.5.
- \*Center of the package: The center is halfway between two pairs of opposite sides, as measured from "B", "B"".